

EIC1415A-8

ISSUED DATE: 09/06/2007

14.40-15.40GHz 8-Watt Internally-Matched Power FET

FEATURES

- 14.40-15.40GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +39.0 dBm Output Power at 1dB Compression
- 5.5 dB Power Gain at 1dB Compression
- 26% Power Added Efficiency
- -42 dBc IM3 at Po = 28.5 dBm SCL
- 100% Tested for DC, RF, and R_{TH}



ELECTRICAL CHARACTERISTICS (T_a = 25°C)



Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS ¹		TYP	MAX	UNITS
P _{1dB}	Output Power at 1dB Compression f = 14.4-15.4GHz V_{DS} = 10 V, $I_{DSQ} \approx 2200$ mA	38.0	39.0		dBm
G _{1dB}	Gain at 1dB Compression $f = 14.4-15.4$ GHz $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 2200$ mA	4.5	5.5		dB
ΔG	Gain Flatness $f = 14.4-15.4GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 2200\text{mA}$			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression V _{DS} = 10 V, I _{DSQ} ≈ 2200mA f =14.4-15.4GHz		26		%
Id _{1dB}	Drain Current at 1dB Compression f=14.4-15.4GHz		2300	2600	mA
IM3	Output 3rd Order Intermodulation Distortion Δf = 10 MHz 2-Tone Test; Pout = 28.5 dBm S.C.L ² V_{DS} = 10 V, I_{DSQ} ≈ 65% IDSS f = 15.4GHz	-38	-42		dBc
I _{DSS}	Saturated Drain Current $V_{DS} = 3 \text{ V}, V_{GS} = 0 \text{ V}$		4000	5000	mA
V_P	Pinch-off Voltage $V_{DS} = 3 \text{ V}, I_{DS} = 40 \text{ mA}$		-2.5	-4.0	V
R _{TH}	Thermal Resistance ³		3.5	4.0	°C/W

Note: 1. Tested with 100 Ohm gate resistor.

ABSOLUTE MAXIMUM RATING FOR EFE

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²	
Vds	Drain-Source Voltage	15V	10V	
Vgs	Gate-Source Voltage	-5V	-4V	
lgf	Forward Gate Current	86.4mA	28.8mA	
lgr	Reverse Gate Current	-14.4mA	-4.8mA	
Pin	Input Power	38.5dBm	@ 3dB Compression	
Tch	Channel Temperature	175C	175C	
Tstg	Storage Temperature	-65C to +175C	-65C to +175C	
Pt	Total Power Dissipation	38W	38W	

Note: 1. Exceeding any of the above ratings may result in permanent damage.

^{2.} S.C.L. = Single Carrier Level.

^{3.} Overall Rth depends on case mounting.

^{2.} Exceeding any of the above ratings may reduce MTTF below design goals.

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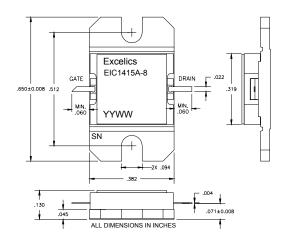
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PACKAGES OUTLINE

Dimensions in inches, Tolerance + .005 unless otherwise specified

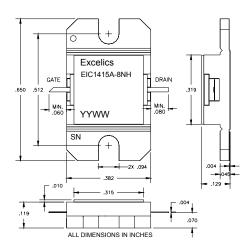
EIC1415A-8 (Hermetic)





Caution! ESD sensitive device.

EIC1415A-8NH (Non-Hermetic)





Caution! ESD sensitive device.

ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC1415A-8	Hermetic	Industrial	14.40-15.40GHz	38.0	-38
EIC1415A-8NH	Non-Hermetic	Industrial	14.40-15.40GHz	38.0	-38

Notes:

- 1. Contact factory for military and hi-rel grades.
- 2. Exact test conditions are specified in "Electrical Characteristics" table.

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